

DETECTOR UPGRADE SEQUENCE

from G1401081

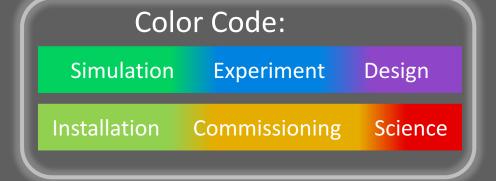
Cosmic Explorer R&D + Design

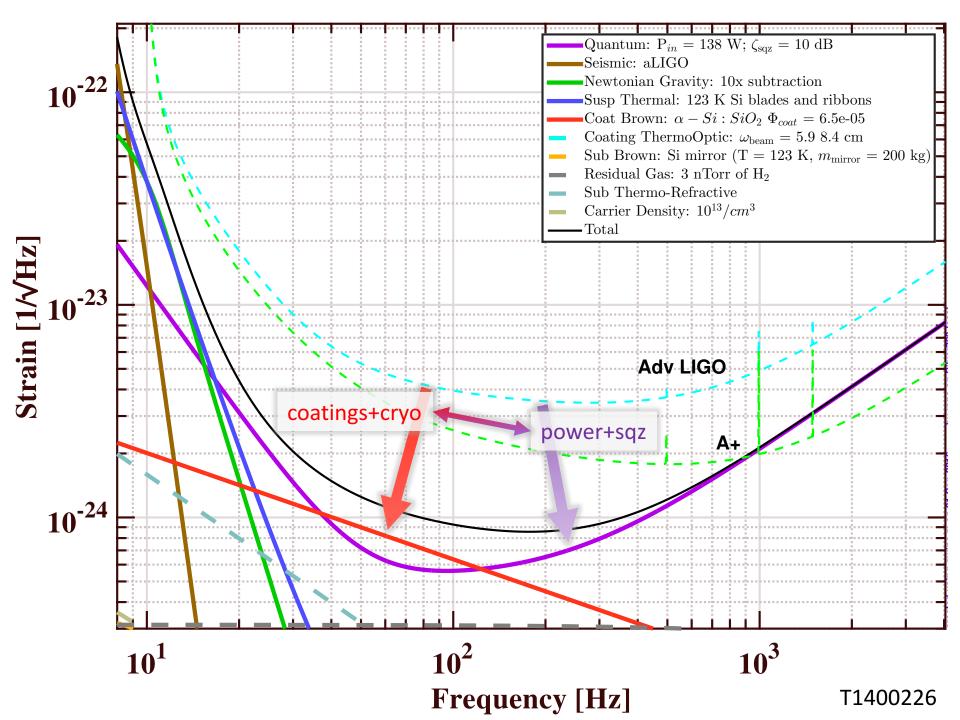
Cryo, Si, 2μm R&D

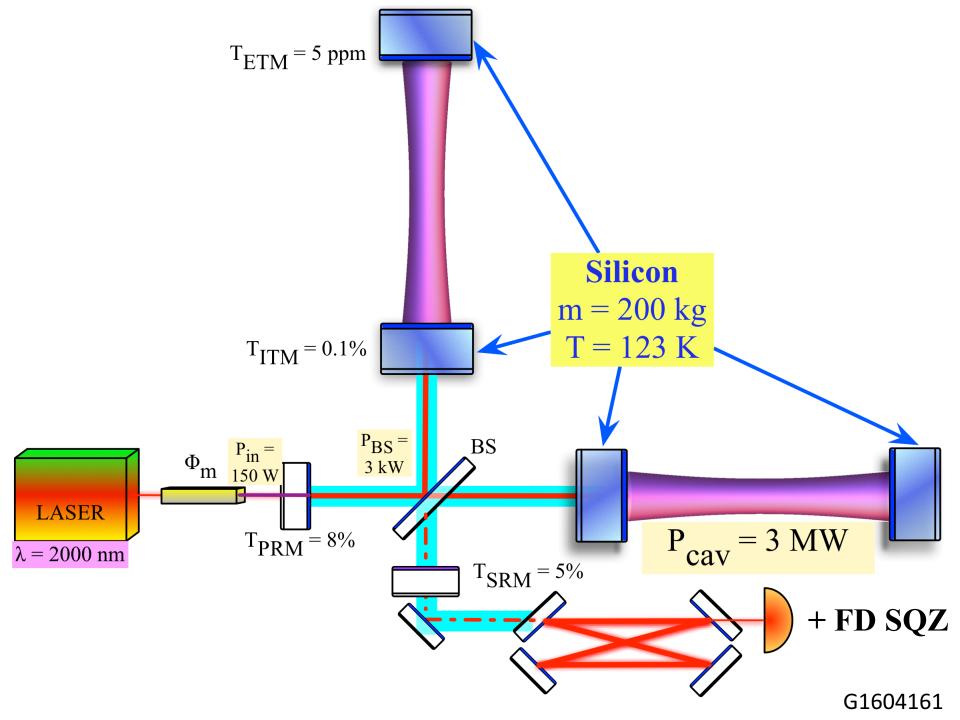
Coating, Sqz R&D

Advanced LIGO

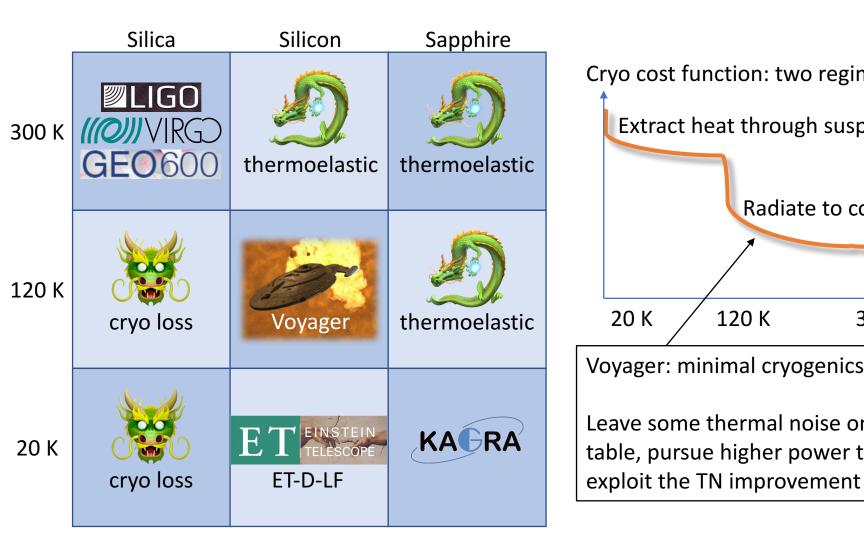
Now

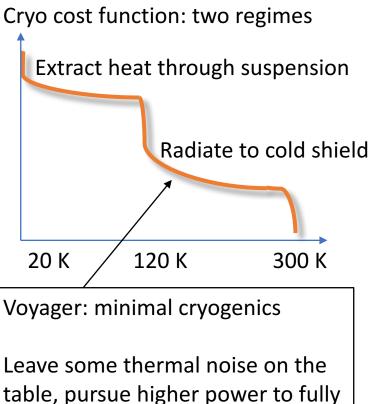






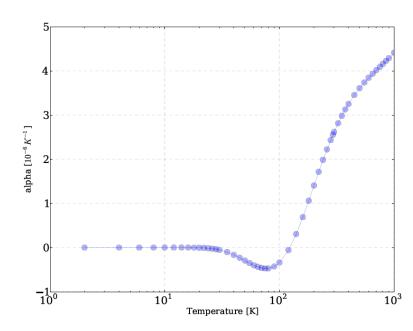
CRYO-OPTICS LANDSCAPE

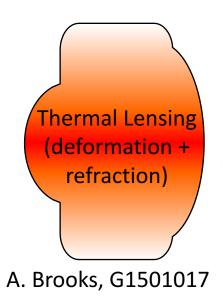




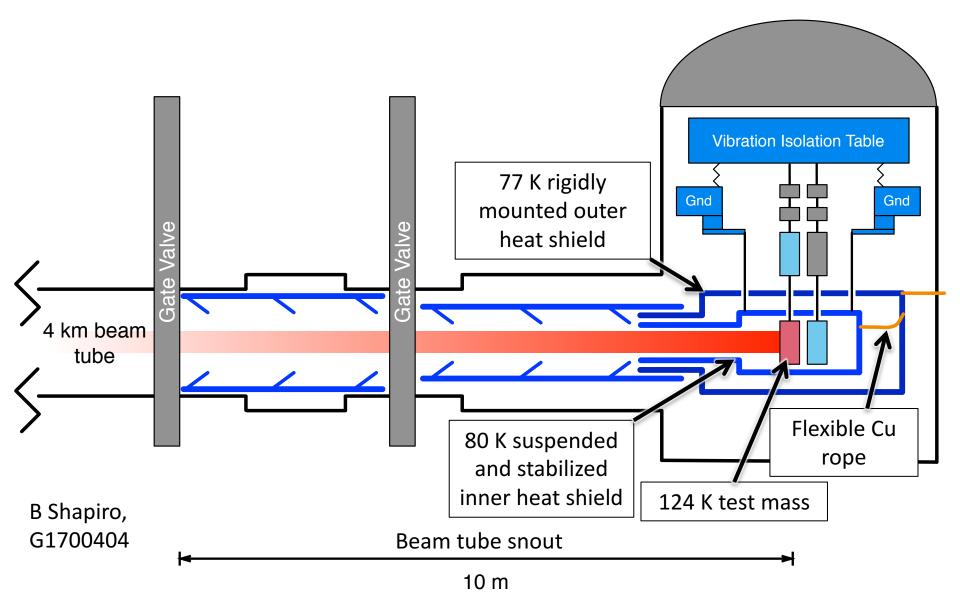
WHY SILICON

- As with sapphire:
 - No cryogenic loss peak
 - High thermal conductivity
- Thermal expansion coeff $\alpha \rightarrow 0$ for $T \sim 120$ K
- Thermal deformation and thermoelastic noise both vanish
- Minimal thermal lensing +
 Minimal cryo @ 120 K
 => Opportunity for high power

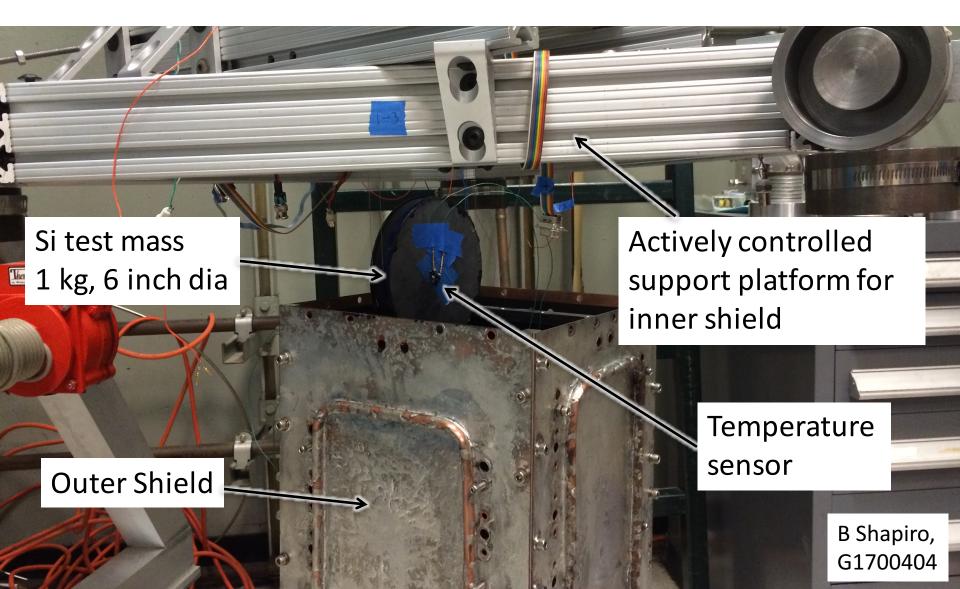




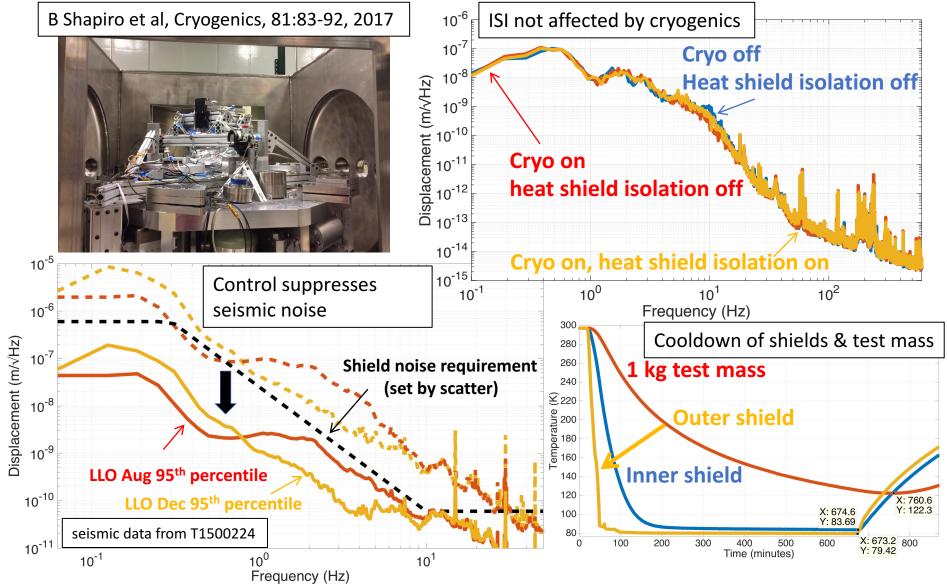
CRYO DESIGN FOR VOYAGER

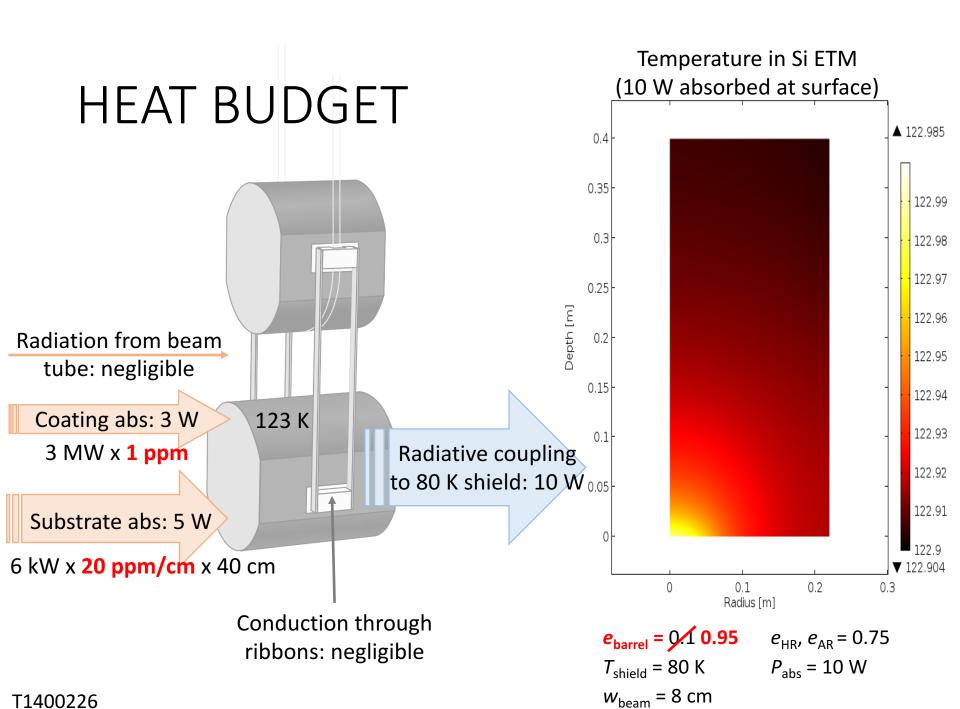


CRYO PROTOTYPE @ STANFORD



CRYO PROTOTYPE @ STANFORD





BARREL COATINGS

Vantablack artistic license:

The Worlds "Blackest Black" and the Hilarious
Artist Feud Behind It

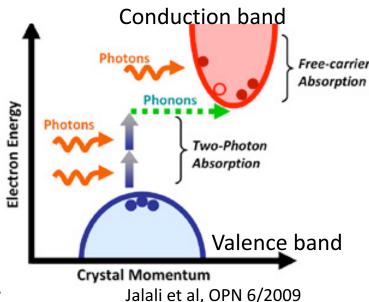
- Several options on the market
 - Acktar Black, Surrey Vantablack, Goddard coating, DLC
 - Aimed at e.g. spacecraft thermal management
- Detailed look at the Acktar coating
 - e \approx 0.85, $\varphi \approx 3.1 \times 10^{-3}$
 - Projects to ~1.5x below coating noise
 - Silver lining: reduced Q for acoustic modes?
 - Abernathy et al, CQG 33 185002 (2016)
- Alternatives are now being evaluated



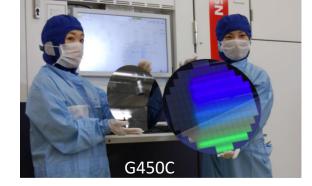


ABSORPTION IN SILICON

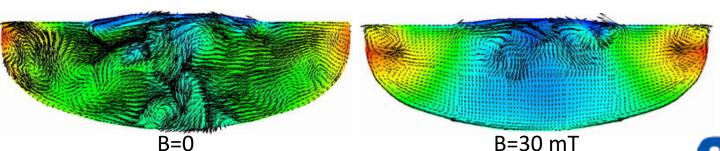
- Requirement was 20 ppm/cm (so input mirror does not overheat)
- Inter-band, 1 photon
 - Photon with ~1 band gap of energy excites a carrier to the conduction band
 - Band gap is $\lambda \sim 1.1 \, \mu m$ => pick a new laser wavelength
 - Negligible effect for $\lambda \gtrsim 1.5 \ \mu m$
- Inter-band, 2 photon
 - Two photons combine to excite a carrier
 - Non-linear, power dependent process
 - Seems OK for our power density levels
- Intra-band, free carrier
 - Photon kicks a free carrier
 - Need to minimize free carrier density
 - Impurities act as unintended dopants
- Several other processes are possible...

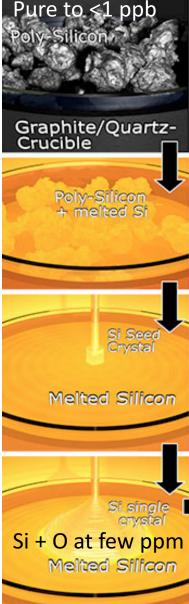


FABRICATION



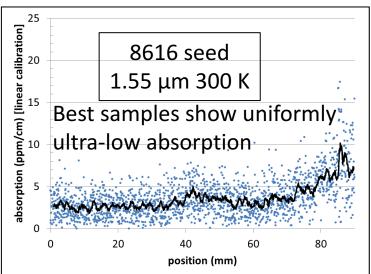
- Very pure mono-crystalline silicon is made commercially by the Czochralski (CZ) process
- Crystals typically grown at 20-30 cm diameter
 - 45 cm/200 kg has been demonstrated
- Main impurity is oxygen (from silica crucible)
 - Trace amounts of carbon, boron, phosphorus
- Magnetic CZ process adds B field to modify convection in the melt (limits oxygen transport)

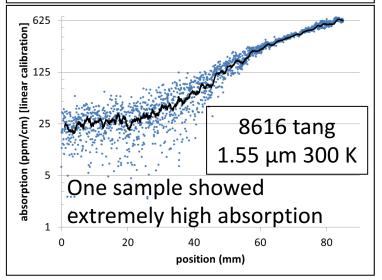




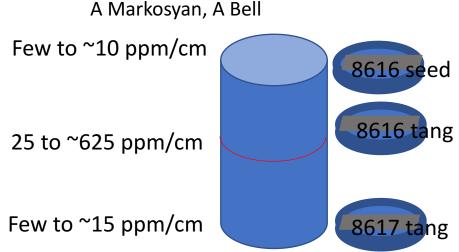


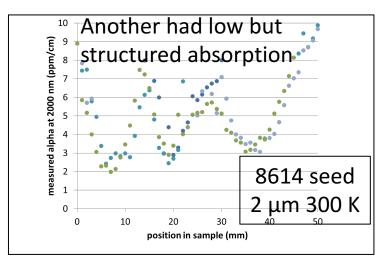
ABSORPTION: 1D RADIAL PROFILE





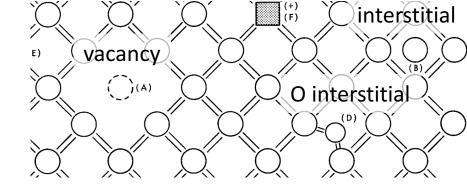




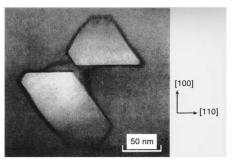


A Markosyan, G1700480

DEFECTS AND SCATTER

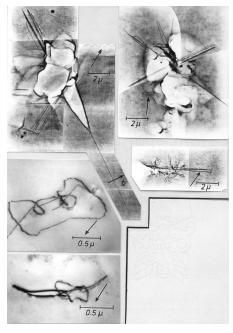


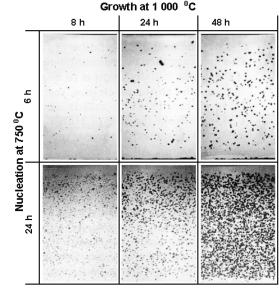
Defect populations depend on crystal growth parameters:



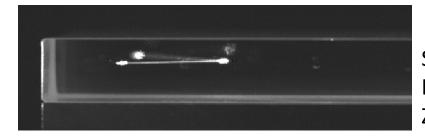
Void defects typically <0.2 µm (vacancy rich)

Dislocation structures (interstitial rich)





SiO₂ precipitate after anneal (O rich) Lower T anneals can create or eradicate free carriers (thermal donors)



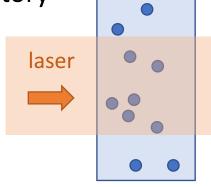
Scatterometry underway at Glasgow InGaAs camera image of MCZ silicon sample Z Tornasi et al, G1700444

NEXT STEPS

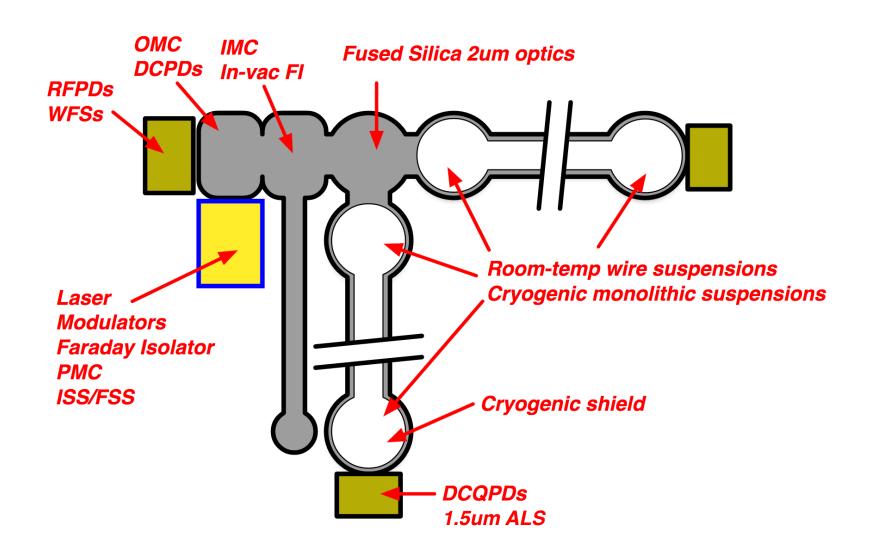
- Cryo technologies
 - Optimization of black coatings and heat straps
 - Rapid cooling system (conductive heat switch)
 - Detailed thermal analysis and mechanical design
- Silicon optics
 - Annealing study
 - Polishing/surface absorption
 - Phase noise
- Integration
 - Caltech 40m lab as Voyager prototype

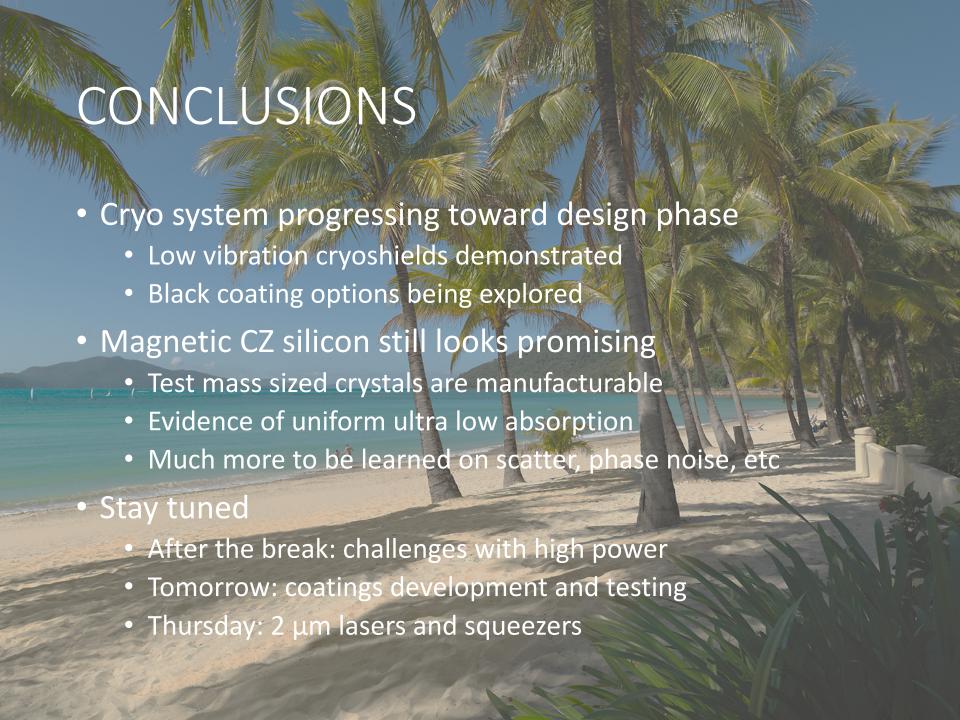
PHASE NOISE IN SEMICONDUCTORS

- All optics impose thermo-refractive noise
 - T dependent refractive index, $\beta = dn/dT...$
 - ...combines with random localized fluctuations in T...
 - ...to produce phase noise
- Additionally, semiconducting optics suffer from carrier density noise (predicted by Heinert et al)
 - Index depends on free carrier density, $\beta_{CD} = dn/dn_e$ (or n_h)...
 - ...combines with random CD fluctuations... same story
 - Effect size grows with carrier density (another motivation to keep impurities low)
- CD noise presently predicted to be negligible
 - Need to check this theory with MCZ Si samples



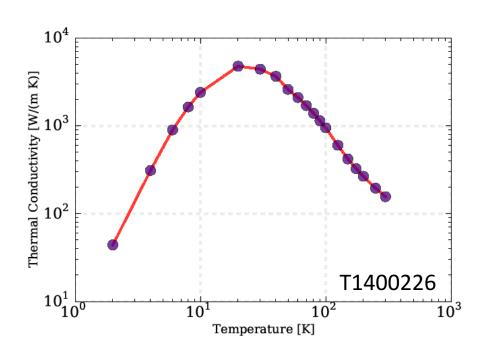
40M PROTOTYPE

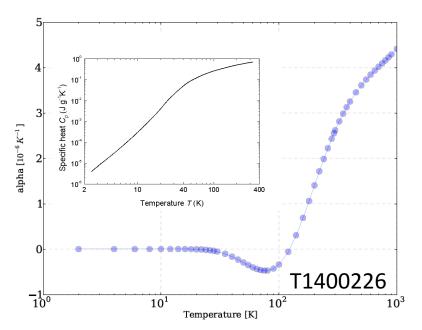


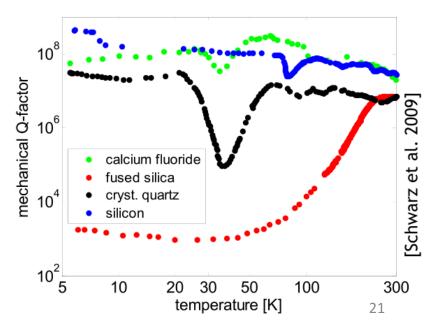


Crystalline Silicon

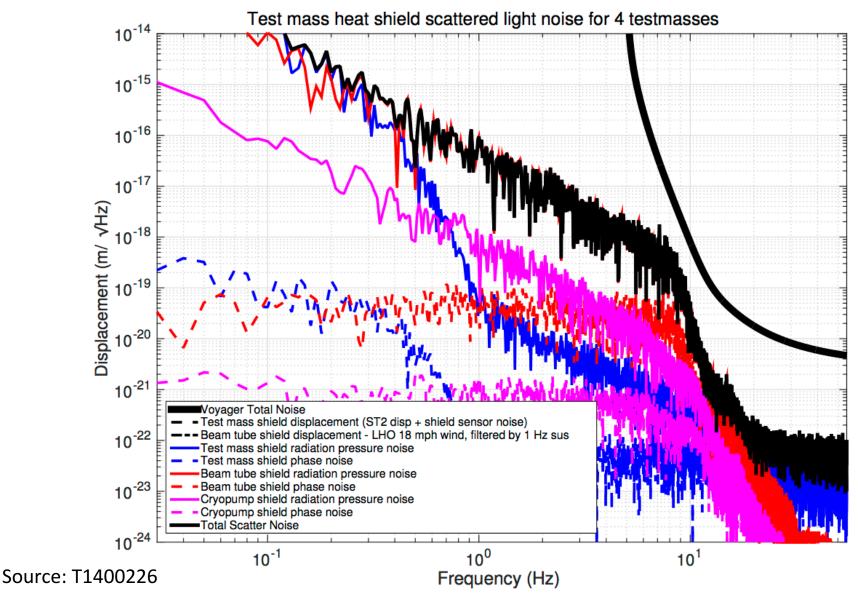
- Zero CTE at 123 K
- Good thermal conductivity
- Low mechanical loss
- Transparent above 1500 nm



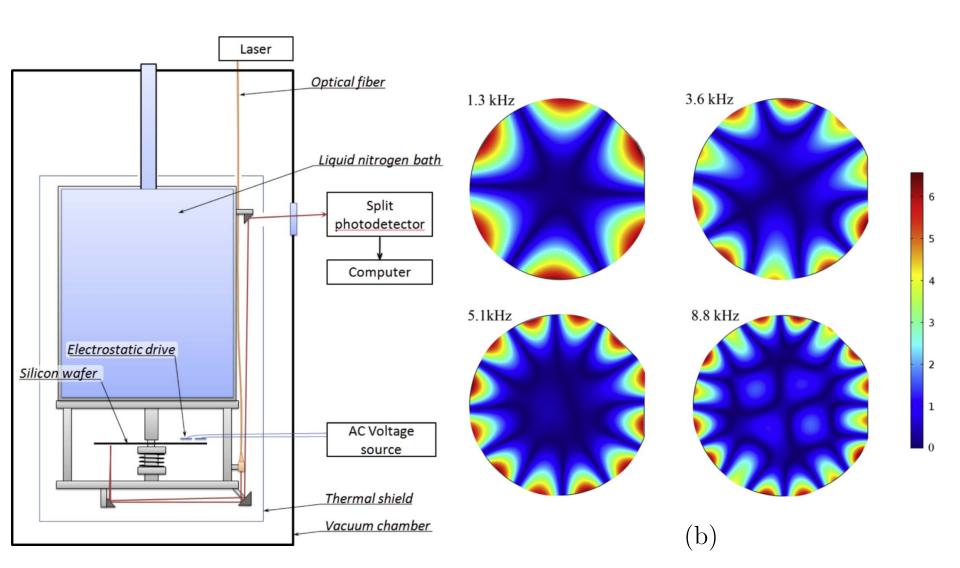




Heat Shield Scatter Estimation



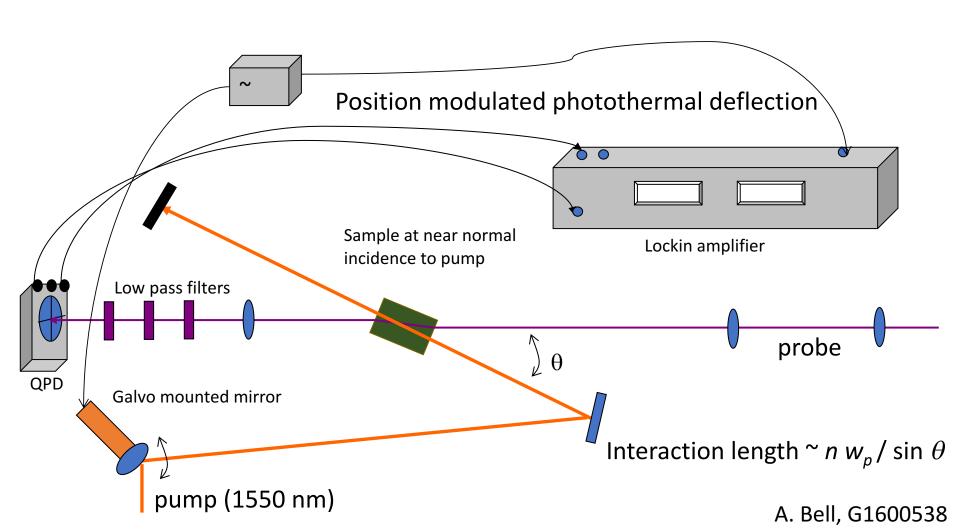
ACKTAR EXPERIMENT



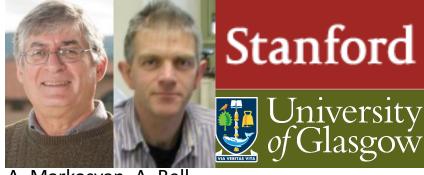
IR ABSORPTION MEASUREMENTS



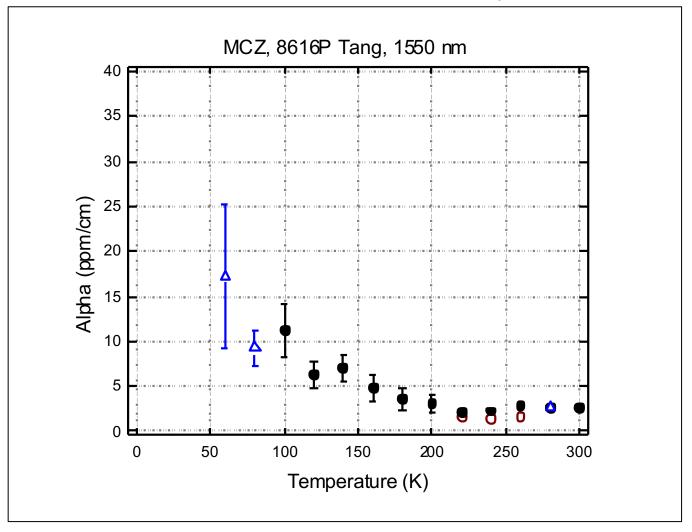
A. Markosyan, A. Bell



IR ABSORPTION RESULTS



A. Markosyan, A. Bell



WHY CRYOGENIC SILICON?

S. Rowan, G000069

Silicon: similar to supphire but coefficient of thermal expansion = 0 at ~ 120K, ~ 20K

Themo-elastic noise -> zero at these temperatures

-> Silicon looks very interesting